

FIRST INTERNATIONAL
SiGe Technology and Device Meeting
(From Materials and Process Technology to Device and Circuit Technology)

NAGOYA, JAPAN, JANUARY 15-17, 2003

<http://www.murota.riec.tohoku.ac.jp/ISTDM2003Jan/>



The first International SiGe Technology and Device Meeting (ISTDM) will be held in Nagoya, Japan, on January 15-17, 2003. This meeting will provide a forum for reviewing and discussing all technological aspects from materials and process technologies to device and circuit technologies for SiGe(C) semiconductor. The meeting will consist of both invited and contributed papers. Contributed papers are solicited in the following areas;

Technical Area

- 1. Materials in Si-Ge-(C) System:** SiGe wafer fabrication; Strained or Strain-relaxed Si, Ge, SiGe(C) or Si:C formation; Novel growth technique; Si, Ge and SiGe(C) quantum wire/dot formation; Defect-controlled buffer layer growth; Defect engineering and characterization.
- 2. Process Technology:** Gate, source/drain and channel engineering; SiGe(C) and Si:C epitaxy; Polycrystalline/amorphous SiGe(C) and Si:C deposition; Cleaning and treatment of SiGe(C) surface; Impurity doping; Impurity diffusion and diffusion suppression; Dry etching; Metal contact; Si/Ge intermixing control; Oxide and nitride on SiGe heterostructure; Ge and C contamination in Si process; Process characterization.
- 3. Device Technology:** HBT; CMOS; BiCMOS; Hetero-FET over CMOS; RTD; Optical devices (emitters and receivers); Ultimate small device; High-speed devices; Low-voltage/low-power devices; SOI; SoC.
- 4. Circuit Technology:** Analog; RF power amplifier; High-speed; Mixed-analog/digital; RF mobile communication; Wireline data-/tele-communication; Ubiquitous network.

On behalf of the Committees, it is our great pleasure to welcome you to the ISTDM Conference at Nagoya, Japan.

*Yukio Yasuda (Nagoya University)
Chair of the Organizing Committee
for the 1st Meeting*

*Junichi Murota (Tohoku University)
Chair of the International Technical Program Committee
for the 1st Meeting*

SUBMISSION OF ABSTRACTS (Deadline : Extended to **October 10, 2002)**

ONE ORIGINAL and THREE COPIES of camera-ready two-page abstract with one page of text and one page of figures, written in English on white bond paper (A4 size; 2.5cm margin on four sides, **use of Times New Roman Font and Single Spacing is recommended**) should be submitted by **October 10, 2002** to Professor Junichi Murota at Research Institute of Electrical Communication, Tohoku University, Katahira 2-1-1, Aoba-ku, Sendai 980-8577, Japan. **Abstract submission as E-MAIL-ATTACHED WORD-file or PDF-file is also available to SiGe@murota.riec.tohoku.ac.jp**. The abstract text (in normal 12-point font) should be headed by the Title (in bold 14-point font), Author(s), Affiliation(s), Address, Telephone number, Fax number and E-mail address (in normal 12-point font), and clearly describes the new contributions of the work. The submission notification included Title, Author(s), Affiliation(s), Address, Telephone number, Fax number and E-mail address should be also sent by E-mail. Papers to be presented at the meeting will be selected by the Program Committee based on the submitted abstracts. **The notice of acceptance and the advanced program** will be e-mailed to one of the authors by the middle of November 2002. **The proceedings will be published in Applied Surface Science** after this meeting. The submitted proceeding manuscripts will be refereed. **The article should be submitted to the Publication Office on the first day of the meeting.** More information of the conference will be announced on the Web Site (<http://www.murota.riec.tohoku.ac.jp/ISTDM2003Jan/>).

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